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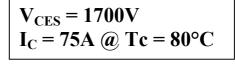


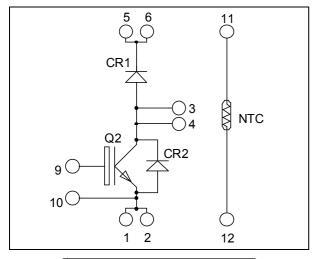


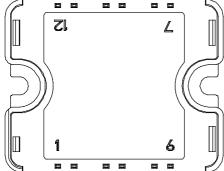




## Boost chopper Trench + Field Stop IGBT3 Power Module







Pins 1/2; 3/4; 5/6 must be shorted together

#### **Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

| Symbol                            | Parameter                             |                      | Max ratings  | Unit |
|-----------------------------------|---------------------------------------|----------------------|--------------|------|
| $V_{CES}$                         | Collector - Emitter Breakdown Voltage |                      | 1700         | V    |
| L ('ontinuous ('ollector ('urrent | Continuous Collector Current          | $T_C = 25^{\circ}C$  | 130          |      |
|                                   | $T_C = 80$ °C                         | 75                   | Α            |      |
| $I_{CM}$                          | Pulsed Collector Current              | $T_C = 25^{\circ}C$  | 150          |      |
| $V_{GE}$                          | Gate – Emitter Voltage                |                      | ±20          | V    |
| $P_{D}$                           | Maximum Power Dissipation             | $T_C = 25^{\circ}C$  | 465          | W    |
| RBSOA                             | Reverse Bias Safe Operating Area      | $T_j = 125^{\circ}C$ | 150A @ 1600V |      |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

| Symbol        | Characteristic                       | Test Conditions                         |                        | Min | Typ | Max | Unit |
|---------------|--------------------------------------|---|------------------------|-----|-----|-----|------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0V, V_{CE} = 1700V$           |                        |     |     | 250 | μΑ   |
| V             | Collector Emitter Saturation Voltage | J OL J                                  | $T_j = 25$ °C          |     | 2.0 | 2.4 | V    |
| $V_{CE(sat)}$ |                                      |   | $T_{j} = 125^{\circ}C$ |     | 2.4 |     | ·    |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}$ , $I_C = 1 \text{mA}$ |                        | 5.0 | 5.8 | 6.5 | V    |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20V, V_{CE} = 0V$             |                        |     |     | 400 | nA   |

### **Dynamic Characteristics**

| Symbol           | Characteristic               | Test Conditions  |                | Min | Typ  | Max | Unit  |
|------------------|------------------------------|--|----------------|-----|------|-----|-------|
| Cies             | Input Capacitance            | $\begin{aligned} V_{GE} &= 0V \\ V_{CE} &= 25V \\ f &= 1MHz \end{aligned}$ |                |     | 6800 |     |       |
| $C_{oes}$        | Output Capacitance           |  |                |     | 277  |     | pF    |
| $C_{res}$        | Reverse Transfer Capacitance |  |                |     | 220  |     |       |
| $T_{d(on)}$      | Turn-on Delay Time           | Inductive Swit   | ching (25°C)   |     | 370  |     |       |
| $T_{r}$          | Rise Time                    | $V_{GE} = 15V$   |                |     | 40   |     |       |
| $T_{d(off)}$     | Turn-off Delay Time          | $V_{\text{Bus}} = 900V$ $I_{\text{C}} = 75A$                               |                |     | 650  |     | ns    |
| $T_{\rm f}$      | Fall Time                    | $R_G = 10\Omega$   |                |     | 180  |     | İ     |
| $T_{d(on)}$      | Turn-on Delay Time           | Inductive Swit   | ching (125°C)  |     | 400  |     |       |
| $T_{r}$          | Rise Time                    | $V_{GE} = 15V$   |                |     | 50   |     |       |
| $T_{d(off)}$     | Turn-off Delay Time          | $V_{\text{Bus}} = 900V$ $I_{\text{C}} = 75A$                               |                |     | 800  |     | ns    |
| $T_{\mathrm{f}}$ | Fall Time                    | $R_G = 6.8\Omega$  |                |     | 300  |     |       |
| Eon              | Turn-on Switching Energy     | $V_{GE} = 15V$ $V_{Bus} = 900V$  | $T_j = 125$ °C |     | 24   |     | I ees |
| $E_{\text{off}}$ | Turn-off Switching Energy    | $I_C = 75A$ $R_G = 6.8\Omega$  | $T_j = 125$ °C |     | 23.5 |     | mJ    |

## Chopper diode ratings and characteristics

| Symbol          | Characteristic                          | Test Conditions                                     | Test Conditions        |      | Тур  | Max | Unit |
|-----------------|---|---|------------------------|------|------|-----|------|
| $V_{RRM}$       | Maximum Peak Repetitive Reverse Voltage |   |                        | 1700 |      |     | V    |
| $I_{RM}$        | Maximum Reverse Leakage Current         | $V_{R} = 1700V$                                     | $T_j = 25$ °C          |      |      | 250 | μA   |
| 1 <sub>RM</sub> |   | V <sub>R</sub> -1700 V                              | $T_j = 125$ °C         |      |      | 500 | μΛ   |
| $I_{F}$         | DC Forward Current                      |   | $Tc = 80^{\circ}C$     |      | 75   |     | A    |
| $V_{\rm F}$     | Diode Forward Voltage                   | $I_F = 75A$   | $T_j = 25$ °C          |      | 1.8  | 2.2 | V    |
| * F             | Blode I of ward Voluge                  |   | $T_{i} = 125^{\circ}C$ |      | 1.9  |     | ,    |
| $t_{rr}$        | Reverse Recovery Time                   |   | $T_j = 25^{\circ}C$    |      | 385  |     | ns   |
| ۲rr             | Reverse Recovery Time                   |   | $T_{j} = 125^{\circ}C$ |      | 490  |     | 113  |
| $Q_{rr}$        | Reverse Recovery Charge                 | $I_F = 75A$<br>$V_R = 900V$<br>$di/dt = 800A/\mu s$ | $T_j = 25^{\circ}C$    |      | 19   |     | μС   |
| Qrr             | Reverse Recovery Charge                 |   | $T_{j} = 125^{\circ}C$ |      | 31   |     | μ    |
| Б               | D                                       |   | $T_j = 25$ °C          |      | 9    |     | mJ   |
| $E_{r}$         | Reverse Recovery Energy                 |   | $T_{i} = 125^{\circ}C$ |      | 17.5 |     | 111J |



#### Thermal and package characteristics

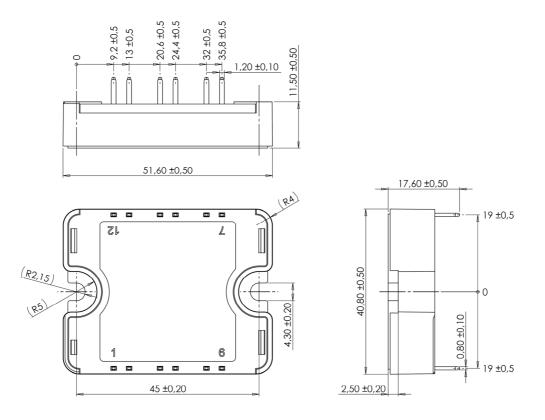
| Symbol            | Characteristic  |             |      | Min  | Тур | Max  | Unit |
|-------------------|---|-------------|------|------|-----|------|------|
| $R_{\text{thJC}}$ | Junction to Case Thermal Resistance                           |             | IGBT |      |     | 0.27 | °C/W |
|                   | Diode   | Diode       |      |      | 0.5 | C/ W |      |
| $V_{ISOL}$        | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz |             |      | 4000 |     |      | V    |
| $T_{J}$           | Operating junction temperature range                          |             |      | -40  |     | 150  |      |
| $T_{STG}$         | Storage Temperature Range                                     |             |      | -40  |     | 125  | °C   |
| $T_{\rm C}$       | Operating Case Temperature                                    | -40         |      | 100  |     |      |      |
| Torque            | Mounting torque   | To heatsink | M4   | 2    |     | 3    | N.m  |
| Wt                | Package Weight  | •           |      |      |     | 80   | g    |

### Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol             | Characteristic              | Min | Тур  | Max | Unit |
|--------------------|-----------------------------|-----|------|-----|------|
| R <sub>25</sub>    | Resistance @ 25°C           |     | 50   |     | kΩ   |
| B <sub>25/85</sub> | $T_{25} = 298.15 \text{ K}$ |     | 3952 |     | K    |

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature } \\ R_{T}: \text{ Thermistor value at T}$$

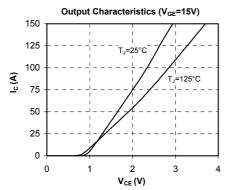
### SP1 Package outline (dimensions in mm)

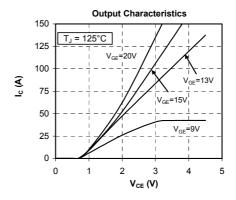


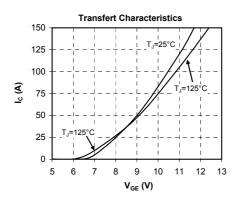
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

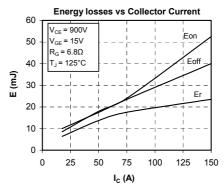


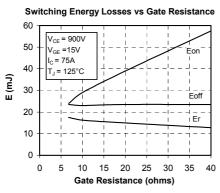
### **Typical Performance Curve**

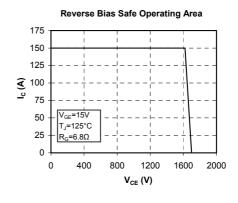


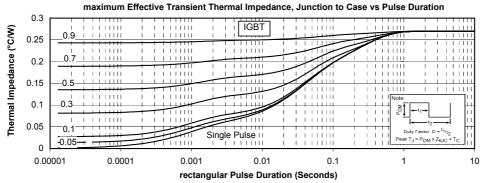




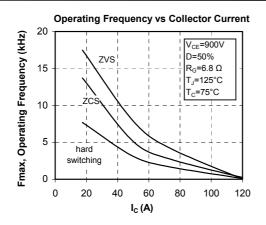


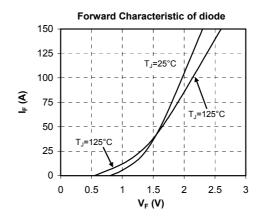


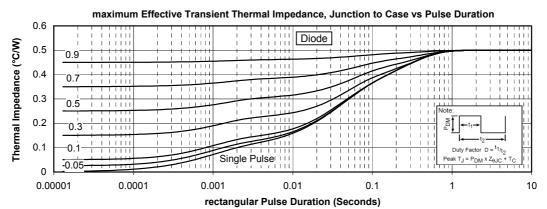












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